WORKSHOP ON NUMERICAL MODELING OF PROCESSES AND DEVICES FOR INTEGRATED CIRCUITS

Santa Clara, California

Nov. 13-14, 1986

CALL FOR PAPERS

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Under the joint sponsorship of the Circuits and Systems Society of the IEEE and in conjunction with ICCAD, a workshop on the numerical modeling of processes and devices for integrated circuits will be held in Santa Clara, CA on Thursday, Nov. 13, 1986 through Friday, Nov. 14, 1986.

The program will consist of 20-minute presentations selected from descriptive extended abstracts. Topics could include: process simulation; device modeling and simulation of complex structures; device modeling for circuit simulation; algorithms and software; integration of process, device and circuit simulation; simulation of detailed physical phenomena; comparison of simulation for different semiconductor technologies. A workshop environment will be encouraged, and papers should not duplicate ICCAD submissions.

THE DEADLINE FOR ABSTRACT SUBMISSION IS MAY 31, 1986. Abstracts should include a brief summary statement (50 words) and a more detailed description not to exceed 500 words or two pages including figures. Applicants will be notified of the committee's decision by August 15, 1986. Prospective speakers should send ten copies of their extended abstracts to:

Robert W. Dutton
AEL 204
Stanford University
Stanford, CA 94305
(415) 497-4138

All speakers will have the opportunity to publish a written version of their presentation, subject to review, in a future issue of the IEEE Transactions on Computer-Aided Design of Integrated Circuits and Systems. Deadline for submission of manuscripts will be January 1, 1987. Manuscripts should be sent to Robert W. Dutton.

Final program and meeting details will be mailed in September, 1986.

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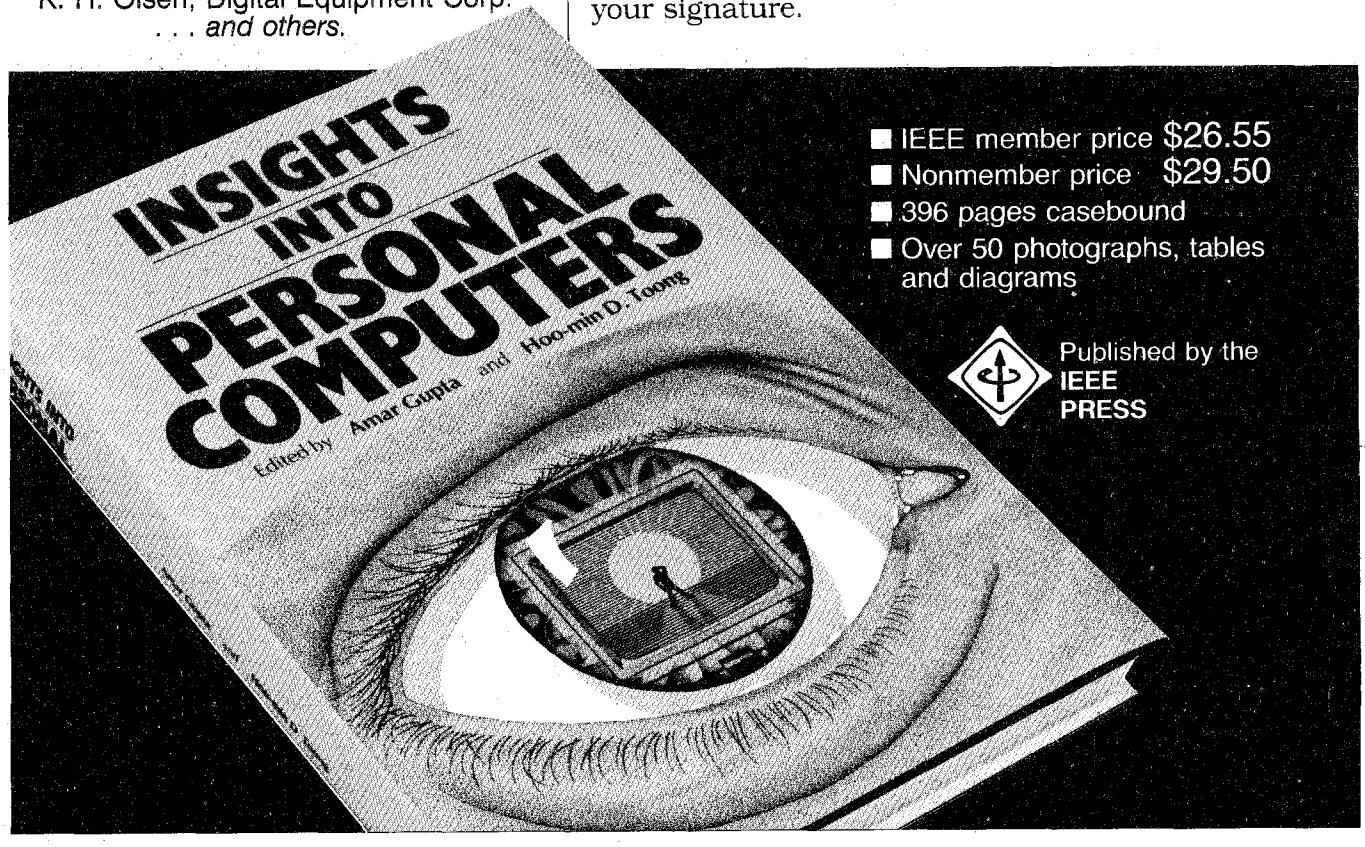

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